

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of : Seiji SARAYAMA, et al.

Serial No. : Div. of 09/590,063 Group Art Unit:

Date Filed : Concurrently Herewith Examiner:

For : PRODUCTION of a GaN BULK CRYSTAL SUBSTRATE AND A  
SEMICONDUCTOR DEVICE FORMED ON A GaN BULK  
CRYSTAL SUBSTRATE VIDEO STILL CAMERA

1185 Avenue of the Americas  
New York, N.Y. 10036

Commissioner For Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450  
**Mail Stop Divisional Appln.**

**INFORMATION DISCLOSURE STATEMENT**

Sir:

The information listed in the attached form PTO-1449 is brought to the attention of the Examiner.

It is respectfully requested that the information cited in annexed Form PTO-1449 be considered by the Examiner in connection with the above-identified patent application, and that such art be made of record in said application.

The information identified on the attached form PTO-1449 was cited by or submitted to the Patent Office in prior application Serial No. 09/590,063 filed on June 8, 2000 which is relied upon for a filing date under 35 U.S.C. §120. Therefore, pursuant to 37 C.F.R. §1.98(d) copies of the information identified herein are not required.

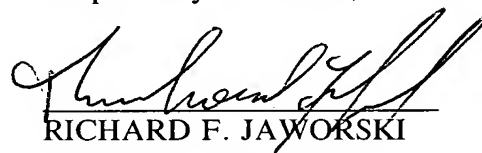
The filing of this Information Disclosure Statement is not an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b).

This Information Disclosure Statement is being filed concurrently with this application.

The Office is hereby authorized to charge any additional fees which may be required for consideration of this Information Disclosure Statement and to credit any overpayment to our Deposit Account No. 03-3125.

Early and favorable consideration of the case is respectfully requested.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Richard F. Jaworski', is written over a horizontal line.

RICHARD F. JAWORSKI  
Registration No. 33,515  
Attorney for Applicants  
Cooper & Dunham LLP  
Tel. (212) 278-0400

Form PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 2271/62289-Z	Serial No. Not Yet Assigned
<b>INFORMATION DISCLOSURE CITATION BY APPLICANT</b> (Use several sheets if necessary)		Applicant <b>Seiji SARAYAMA et al.</b>	
		Filing Date	Group

**U.S. PATENT DOCUMENTS**

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	AA	6 2 7 0 5 6 9	08/2001	Shibata et al.			
	AB	6 1 7 7 0 5 7	01/2001	Purdy			
	AC	5 8 6 8 8 3 7	02/1999	DiSalvo et al.			
	AD						
	AE						
	AF						
	AG						

**FOREIGN PATENT DOCUMENTS**

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AH							
	AI							

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

	AJ	"Preparation of GaN Single Crystals Using a Na Flux", H. Yamane et al., Chemical Mater, 1997, Vol. 9, No. 2, pp. 413-416.
	AK	"InGaN/GaN/AlGaIn-Based Laser Diodes With Cleaved Facets Grown on GaN Substrates", S. Nakamura et al., Applied Physics Letters, 1998, Vol. 73, No. 6, pp. 832-834.
	AL	"Bulk and Homoepitaxial GaN-growth and Characterization", S. Porowski, Journal of Crystal Growth, 1998, Vol. 189/190, pp.153-158.
	AM	"InGaN/GaN/AlGaIn-Based Laser Diodes With Modulation-Doped Strained-Layer Superlattices", S. Nakamura et al., Japanese Journal of Applied Physics, 1997, Vol. 36, No. 12A, pp. 1568-1571.
	AN	

EXAMINER	DATE CONSIDERED
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**\*EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.